

INFLUENCE OF γ -RADIATION ON STRUCTURE OF HIGH DENSITY POLYETHYLENE COMPOSITES WITH GaAs AND GaAs <Te> FILLERS

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This paper presents the results of Fourier-IR spectroscopic studies of γ -radiation effect on the structure of composite films of high density polyethylene (HDPE) with semiconductor fillers of gallium arsenide (GaAs) and gallium arsenide doped with tellurium (GaAs <Te>) at room temperature. IR spectroscopy allows one to follow structural changes due to the influence of gamma radiation and identify patterns associated with these changes.

A homogeneous mixture was prepared from HDPE and GaAs and GaAs <Te> semiconductors powders (with particle size ≈ 50 micron) through mechanical mixing. Then samples were exposed to hot pressing at $T = 413$ K temperature within 15 minutes and cooled to room temperature within 30 min.

The samples were irradiated with γ -rays from a ^{60}Co source at room temperature with a dose rate of $1.05 \text{ Gy} / \text{s}$. The absorbed dose was $\Phi\gamma = 5\text{-}150 \text{ kGy}$.

The Fourier-IR absorption spectra of the initial and γ -irradiated composite samples were recorded on a Varian 640 FT-IR spectrometer at room temperature in the frequency range $4000\text{--}400 \text{ cm}^{-1}$. Structural changes associated with the influence of γ radiation were observed in the frequency range $750\text{--}700 \text{ cm}^{-1}$, corresponding to the pendulum vibration of the CH_2 group of HDPE. The band at 730 cm^{-1} characterizes crystalline regions, and the band at 720 cm^{-1} characterizes crystallites + amorphous layers.

The crystallinity degree of the samples was calculated based on the optical densities by the following formula :

$K =$

where D_{730} and D_{720} are optical density of 730 and 720 cm^{-1} bands in the IR spectra of HDPE + GaAs and HDPE + GaAs <Te> films respectively.

The degree of crystallinity and their correlation along the absorption bands with maximum at 720 and 730 cm^{-1} were determined. By the dose dependence of the relative degree of crystallinity, it was found that in the absorbed dose range $\Phi\gamma = 5\text{-}150 \text{ kGy}$, the HDPE / GaAs <Te> composites are the most radiation-resistant in comparison with the HDPE / GaAs composites.

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